

METHOD FOR FABRICATING A SEMICONDUCTOR STRUCTURE
INCLUDING A METAL OXIDE INTERFACE WITH SILICON

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Abstract of the Disclosure

A method for fabricating a semiconductor structure including the steps of providing a silicon substrate (10) having a surface (12); forming amorphous silicon dioxide (14) on the surface (12) of the silicon substrate (10); providing a metal oxide (18) on the amorphous silicon dioxide (14); heating the semiconductor structure to form an interface comprising a seed layer (20) adjacent the surface (12) of the silicon substrate (10); and forming one or more layers of a high dielectric constant oxide (22) on the seed layer (20).

FIG. 1 to accompany abstract.

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